

# FDS6680S

## 30V N-Channel PowerTrench® SyncFET™

### General Description

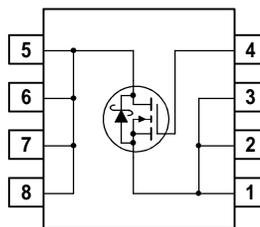
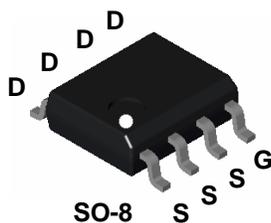
The FDS6680S is designed to replace a single SO-8 MOSFET and Schottky diode in synchronous DC:DC power supplies. This 30V MOSFET is designed to maximize power conversion efficiency, providing a low  $R_{DS(ON)}$  and low gate charge. The FDS6680S includes an integrated Schottky diode using Fairchild's monolithic SyncFET technology. The performance of the FDS6680S as the low-side switch in a synchronous rectifier is indistinguishable from the performance of the FDS6680 in parallel with a Schottky diode.

### Applications

- DC/DC converter
- Motor drives

### Features

- 11.5 A, 30 V.  $R_{DS(ON)} = 0.011 \Omega @ V_{GS} = 10 V$   
 $R_{DS(ON)} = 0.016 \Omega @ V_{GS} = 4.5 V$
- Includes SyncFET Schottky body diode
- Low gate charge (17nC typical)
- High performance trench technology for extremely low  $R_{DS(ON)}$  and fast switching
- High power and current handling capability



### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Rated	Units
V <sub>DSS</sub>	Drain-Source Voltage	30	V
V <sub>GSS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current – Continuous (Note 1a)	11.5	A
	– Pulsed	50	
P <sub>D</sub>	Power Dissipation for Single Operation (Note 1a)	2.5	W
	(Note 1b)	1.2	
	(Note 1c)	1	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	°C/W
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case (Note 1)	25	°C/W

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS6680S	FDS6680S	13"	12mm	2500 units

## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 1\text{ mA}$ , Referenced to $25^\circ\text{C}$		19		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			1	mA
$I_{GSSF}$	Gate–Body Leakage, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate–Body Leakage, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

### On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	1	2	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 1\text{ mA}$ , Referenced to $25^\circ\text{C}$		-3.3		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 10\text{ V}, I_D = 11.5\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 9.5\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 11.5\text{ A}, T_J = 125^\circ\text{C}$		9.5 13.5 17	11 16 23	m $\Omega$
$I_{D(on)}$	On–State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	50			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 11.5\text{ A}$		27		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$		2010		pF
$C_{oss}$	Output Capacitance	$f = 1.0\text{ MHz}$		526		pF
$C_{rss}$	Reverse Transfer Capacitance			186		pF

### Switching Characteristics (Note 2)

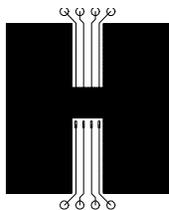
$t_{d(on)}$	Turn–On Delay Time	$V_{DS} = 15\text{ V}, I_D = 1\text{ A},$		10	18	ns
$t_r$	Turn–On Rise Time	$V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$		10	18	ns
$t_{d(off)}$	Turn–Off Delay Time			34	55	ns
$t_f$	Turn–Off Fall Time			14	23	ns
$Q_g$	Total Gate Charge	$V_{DS} = 15\text{ V}, I_D = 11.5\text{ A},$		17	24	nC
$Q_{gs}$	Gate–Source Charge	$V_{GS} = 5\text{ V}$		6.2		nC
$Q_{gd}$	Gate–Drain Charge			5.5		nC

### Drain–Source Diode Characteristics and Maximum Ratings

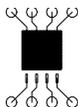
$I_S$	Maximum Continuous Drain–Source Diode Forward Current				3.5	A
$V_{SD}$	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 3.5\text{ A}$ (Note 2) $V_{GS} = 0\text{ V}, I_S = 7\text{ A}$ (Note 2)		0.45 0.6	0.7	V
$t_{rr}$	Diode Reverse Recovery Time	$I_F = 11.5\text{ A},$		20		nS
$Q_{rr}$	Diode Reverse Recovery Charge	$dI_F/dt = 300\text{ A}/\mu\text{s}$ (Note 3)		19.7		nC

#### Notes:

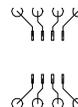
- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a) 50 $^\circ\text{W}$  when mounted on a 1 in $^2$  pad of 2 oz copper



b) 105 $^\circ\text{W}$  when mounted on a .04 in $^2$  pad of 2 oz copper



c) 125 $^\circ\text{W}$  when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width < 300 $\mu\text{s}$ , Duty Cycle < 2.0%
- See "SyncFET Schottky body diode characteristics" below.

## Typical Characteristics

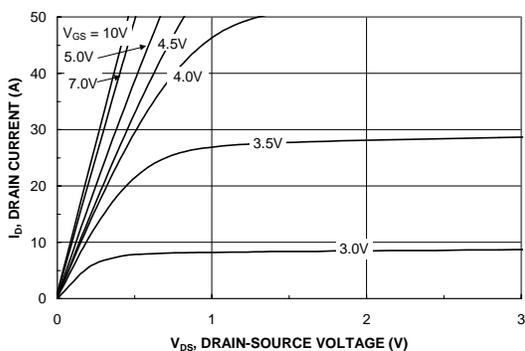


Figure 1. On-Region Characteristics.

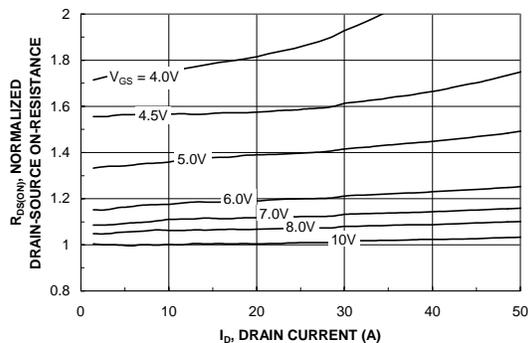


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

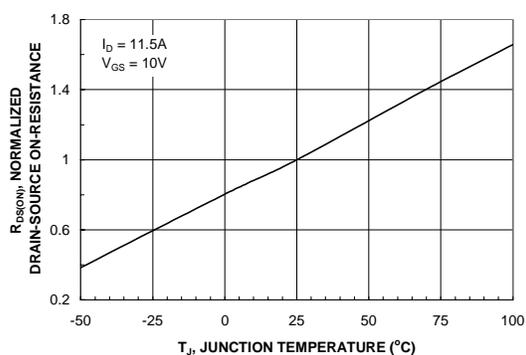


Figure 3. On-Resistance Variation with Temperature.

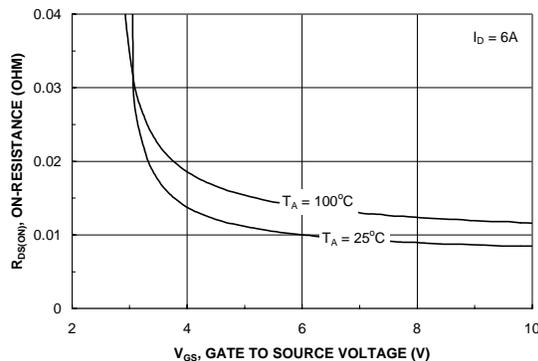


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

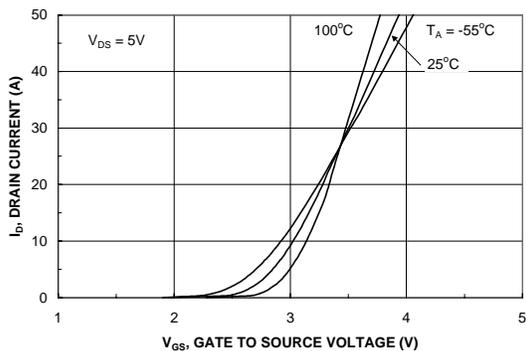


Figure 5. Transfer Characteristics.

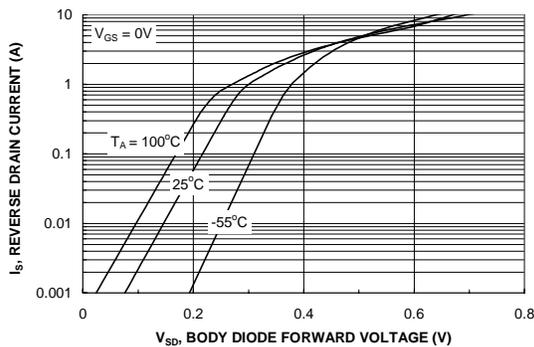
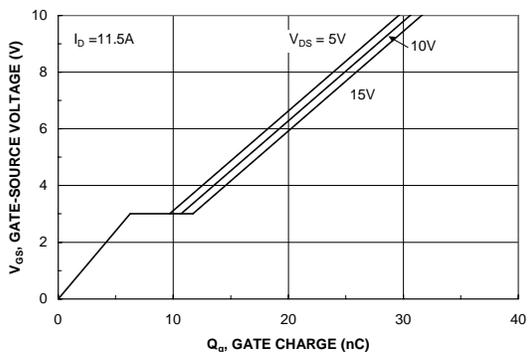
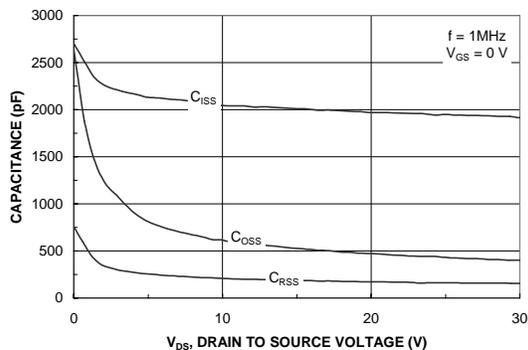


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

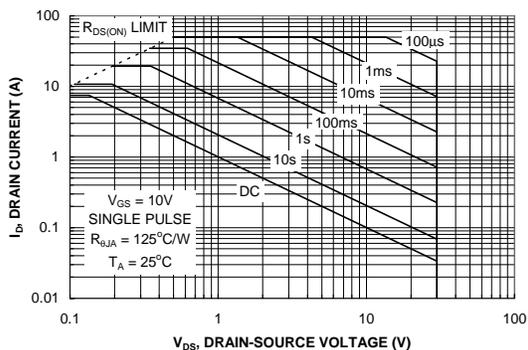
## Typical Characteristics (continued)



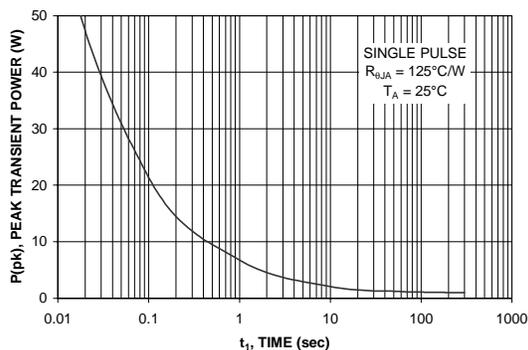
**Figure 7. Gate Charge Characteristics.**



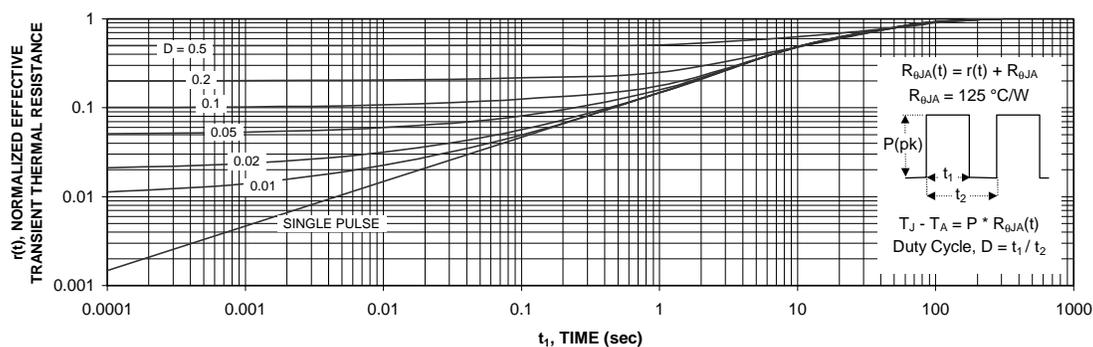
**Figure 8. Capacitance Characteristics.**



**Figure 9. Maximum Safe Operating Area.**



**Figure 10. Single Pulse Maximum Power Dissipation.**



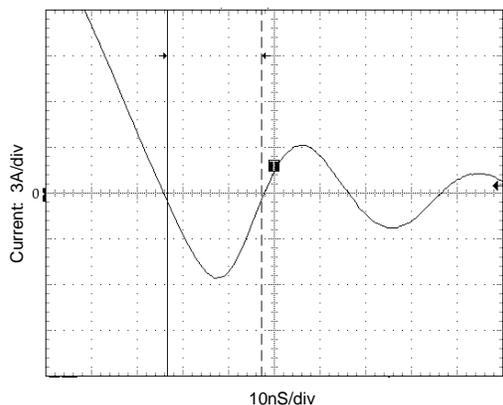
**Figure 11. Transient Thermal Response Curve.**

Thermal characterization performed using the conditions described in Note 1c.  
Transient thermal response will change depending on the circuit board design.

**Typical Characteristics** (continued)

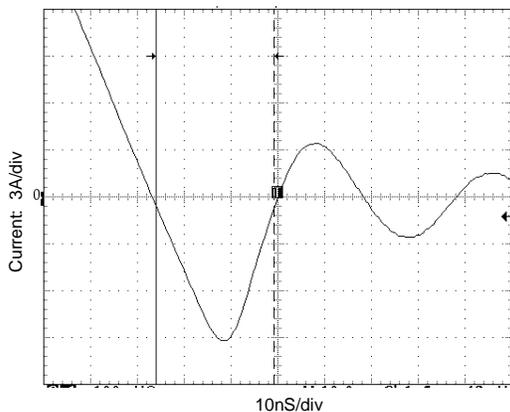
**SyncFET Schottky Body Diode Characteristics**

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 12 shows the reverse recovery characteristic of the FDS6680S.



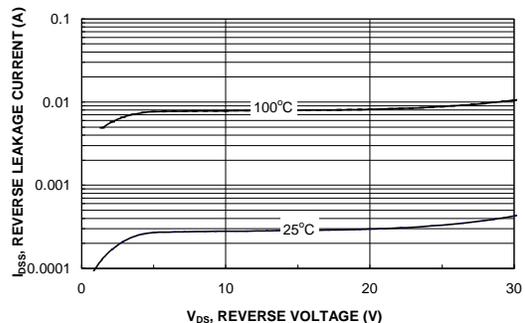
**Figure 12. FDS6680S SyncFET body diode reverse recovery characteristic.**

For comparison purposes, Figure 13 shows the reverse recovery characteristics of the body diode of an equivalent size MOSFET produced without SyncFET (FDS6680).



**Figure 13. Non-SyncFET (FDS6680) body diode reverse recovery characteristic.**

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

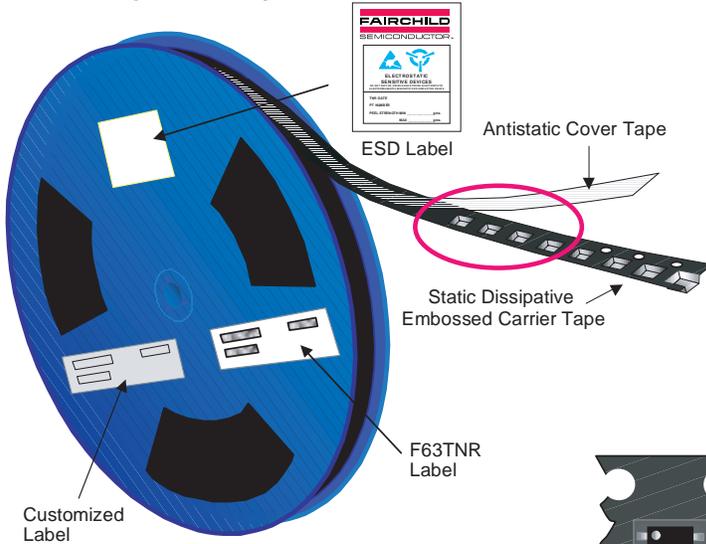


**Figure 14. SyncFET body diode reverse leakage versus drain-source voltage and temperature.**

# SO-8 Tape and Reel Data and Package Dimensions



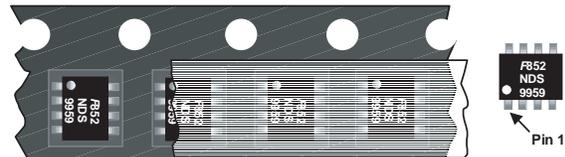
## SOIC(8lds) Packaging Configuration: Figure 1.0



### Packaging Description:

SOIC-8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 330cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 500 units per 7" or 177cm diameter reel. This and some other options are further described in the Packaging Information table.

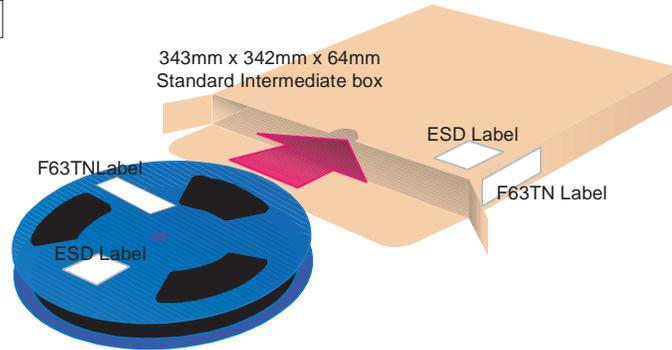
These full reels are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.



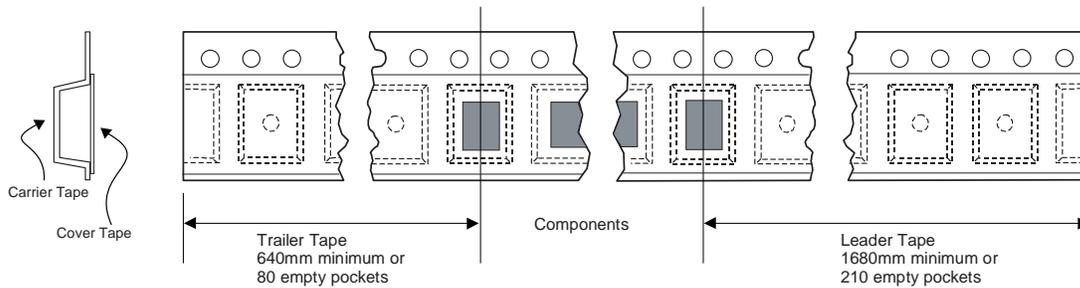
### SOIC-8 Unit Orientation

SOIC (8lds) Packaging Information				
Packaging Option	Standard (no flow code)	L86Z	F011	D84Z
Packaging type	TNR	Rail/Tube	TNR	TNR
Qty per Reel/Tube/Bag	2,500	95	4,000	500
Reel Size	13" Dia	-	13" Dia	7" Dia
Box Dimension (mm)	343x64x343	530x130x83	343x64x343	184x187x47
Max qty per Box	5,000	30,000	8,000	1,000
Weight per unit (gm)	0.0774	0.0774	0.0774	0.0774
Weight per Reel (kg)	0.6060	-	0.9696	0.1182
Note/Comments				

### F63TNR Label sample



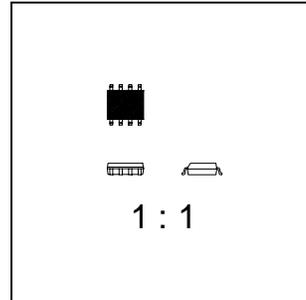
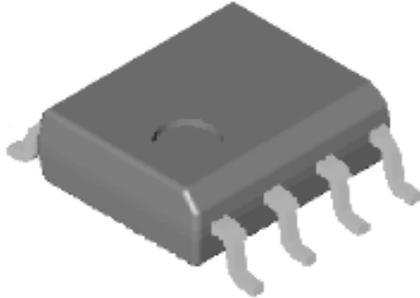
## SOIC(8lds) Tape Leader and Trailer Configuration: Figure 2.0





SO-8 Tape and Reel Data and Package Dimensions, continued

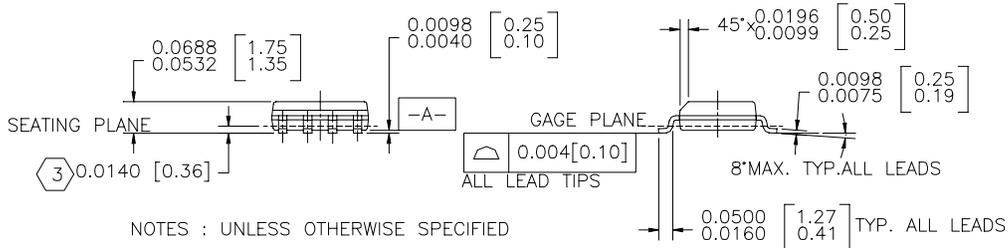
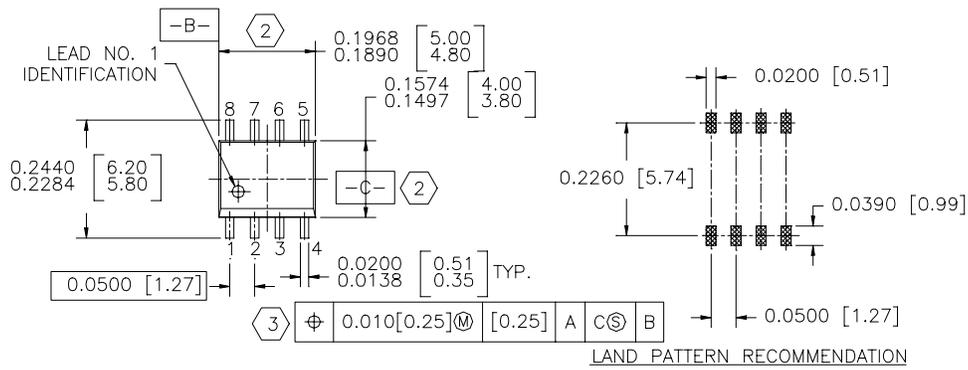
SOIC-8 (FS PKG Code S1)



Scale 1:1 on letter size paper

Dimensions shown below are in:  
inches [millimeters]

Part Weight per unit (gram): 0.0774



NOTES : UNLESS OTHERWISE SPECIFIED

1. STANDARD LEAD FINISH:  
200 MICROINCHES / 5.08 MICRONS MINIMUM  
LEAD / TIN (SOLDER) ON COPPER.

SO 0.150 WIDE 8 LEADS

2. THESE DIMENSIONS DO NOT INCLUDE MOLD FLASH

3. MAXIMUM LEAD 0.024 [0.609]

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CoolFET™	MICROWIRE™	TinyLogic™
CROSSVOLT™	POP™	UHC™
E <sup>2</sup> CMOS™	PowerTrench®	VCX™
FACT™	QFET™	
FACT Quiet Series™	QS™	
FAST®	Quiet Series™	
FASTr™	SuperSOT™-3	
GTO™	SuperSOT™-6	
HiSeC™	SuperSOT™-8	

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## PRODUCT STATUS DEFINITIONS

### Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.